

Transient Voltage Suppressors for ESD Protection

General Description

The LESD9D5.0CT5G is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

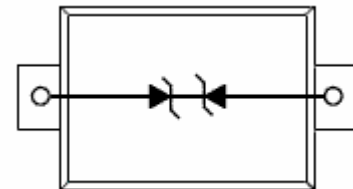
Features

- Small Body Outline Dimensions
- Low Body Height
- Peak Power up to 150 Watts @ 8 x 20 μ s Pulse
- Low Leakage current
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- IEC61000-4-4 Level 4 EFT Protection
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

Absolute Ratings (T_{amb}=25°C)

Symbol	Parameter	Value	Units
P _{PP}	Peak Pulse Power (t _p = 8/20 μ s)	150	W
T _L	Maximum lead temperature for soldering during 10s	260	°C
T _{stg}	Storage Temperature Range	-55 to +155	°C
T _{op}	Operating Temperature Range	-40 to +125	°C
T _j	Maximum junction temperature	150	°C
	IEC61000-4-2 (ESD) air discharge	±15	KV
	contact discharge	±8	
	IEC61000-4-4 (EFT)	40	A
	ESD Voltage Per Human Body Model	16	KV

LESD9D5.0CT5G
S-LESD9D5.0CT5G



We declare that the material of product compliance with RoHS requirements.

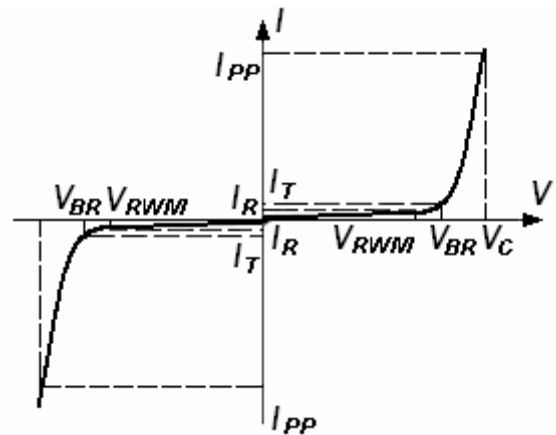
Ordering information

Device	Marking	Shipping
LESD9D5.0CT5G S-LESD9D5.0CT5G	C	8000/Tape&Reel

LESD9D5.0CT5G , S-LESD9D5.0CT5G

Electrical Parameter

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
I_T	Test Current
V_{BR}	Breakdown Voltage @ I_T



Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Device	V_{RWM} (V)	I_{R1} (uA) @ V_{RWM}	I_{R2} (uA) @ $V_R=3.5V$	V_{BR} (V) @ I_T (Note 1)	I_T	V_C (V) @ $I_{PP}=5 A^*$	V_C (V) @ Max I_{PP}^*	I_{PP} (A)*	P_{PK} (W)*	C (pF)
	Max	Max	Max	Min	mA	Typ	Max	Max	Max	Typ
LESD9D5.0CT5G	5.0	0.5	0.3	5.6	1.0	11.6	18.6	9.4	174	15

*Surge current waveform per Figure 1.

1. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

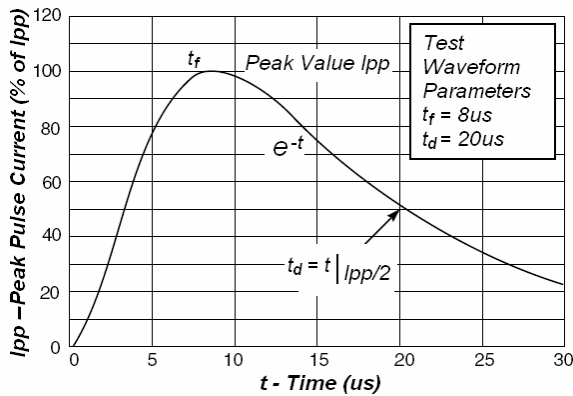


Fig1. Pulse Waveform

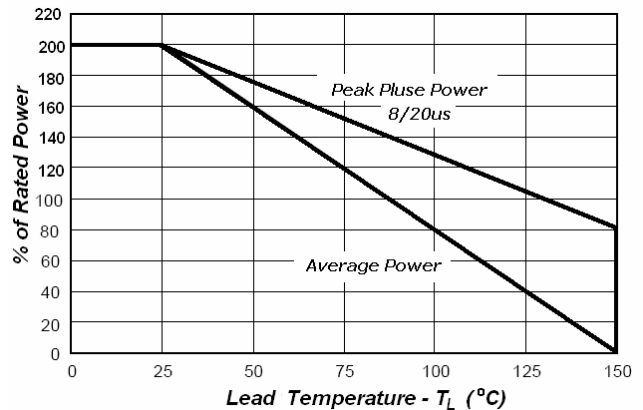
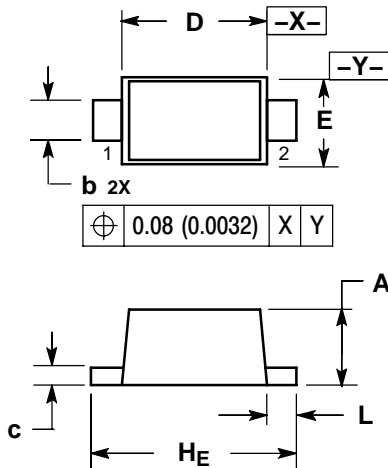


Fig2. Power Derating Curve

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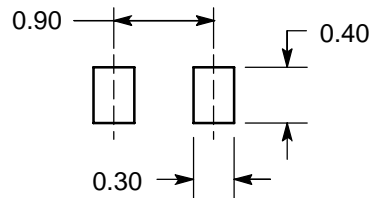


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS